## ABSTRACT OF THE DISCLOSURE

A semiconductor device test probe having a tip portion for being urged against an electrode pad of an integrated semiconductor device to establish an electrical contact against the electrode pad for testing functions of the semiconductor device. The spherical tip portion has a radius of curvature r expressed by 9t  $\leq r \leq$  35t, where r is the radius of curvature of the spherical surface and t is the thickness of the electrode pad. The tip portion may have a first curved surface substantially positioned in the direction of slippage of the probe when the probe is urged against the electrode pad and slipped relative to the electrode pad and a second curved surface opposite to the first curved surface. The first curved surface has a radius of curvature of from  $7 \mu m$  to 30 µm and larger than that of the second curved surface. The test probe may be manufactured by a method comprising the steps of roughing the tip portion of the curved surface by abrasing by means of electrolyte abrasion or abrasing particles to form a symmetrical spherical curved surface, and finishing the tip portion by sliding it on an abrasive member comprising an elastically deformable thick film fixed to a substrate and having abrasive particles therein or thereon directly or through a metallic film.